

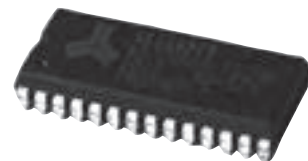
ALLIANCE MEMORY Fast, Low Power SRAMs & DRAMs



This product is RoHS compliant.

Alliance Memory, Inc. acquired the Fast Asynchronous Product line from Alliance Semiconductor. The acquisition includes manufacturing rights, mask sets, IP, design database, the patent rights and the Fast SRAM inventory. The product line-up includes densities ranging from 64k to 4M Fast SRAM in both the x8 and x16 configuration. The company strategy will focus on these "legacy" memories to support the industrial and communications market space.

Alliance Memory, Inc. is a fabless semiconductor company. It has continued the relationships with all of its manufacturing partners that were well established with Alliance Semiconductor. Alliance will soon be introducing new products and will expand its foundry partners. Alliance is also looking at acquiring additional Memory suppliers to expand its portfolio.



RoHS Compliant

For quantities greater than listed, call for quote.

MOUSER STOCK NO.	Alliance Memory Part No.	Package	Density	Organization	Speed (ns)	Temperature Range (°C)	Operating Voltage (V)	Price Each		
								1	25	50
913-AS7C164-15JCN	AS7C164-15JCN	SOJ-28	64K	8Kx8	12	0 to 70	4.5 to 5.5	1.38	1.37	1.35
913-AS7C256A-12JCN	AS7C256A-12JCN	SOJ-28	256K	32Kx8	12	0 to 70	4.5 to 5.5	1.15	1.14	1.13
913-AS7C256A-12TCN	AS7C256A-12TCN	TSOP I-28	256K	32Kx8	12	0 to 70	4.5 to 5.5	1.15	1.14	1.13
913-AS7C3256A-12JCN	AS7C3256A-12JCN	SOJ-28	256K	32Kx8	12	0 to 70	3.0 to 3.6	1.15	1.14	1.13
913-AS7C3256A-12TCN	AS7C3256A-12TCN	TSOP I-28	256K	32Kx8	12	0 to 70	3.0 to 3.6	1.15	1.14	1.13
913-AS7C513-12TCN	AS7C513-12TCN	TSOP II-44	512K	32Kx16	12	0 to 70	4.5 to 5.5	1.91	1.89	1.86
913-AS7C3513-12TCN	AS7C3513-12TCN	TSOP II-44	512K	32Kx16	12	0 to 70	3.0 to 3.6	1.91	1.89	1.86
913-AS7C1024B-12JCN	AS7C1024B-12JCN	SOJ-32	1M	125Kx8	12	0 to 70	4.5 to 5.5	1.91	1.89	1.86
913-AS7C1024B-12TCN	AS7C1024B-12TCN	TSOP I-32	1M	125Kx8	12	0 to 70	4.5 to 5.5	1.91	1.89	1.86
913-AS7C1024B-12TJCN	AS7C1024B-12TJCN	SOJ-32	1M	125Kx8	12	0 to 70	4.5 to 5.5	1.91	1.89	1.86
913-AS7C1025B-12JCN	AS7C1025B-12JCN	SOJ-32	1M	125Kx8	12	0 to 70	4.5 to 5.5	1.91	1.89	1.86
913-AS7C1026B-12JCN	AS7C1026B-12JCN	SOJ-32	1M	64Kx16	12	0 to 70	4.5 to 5.5	1.91	1.89	1.86
913-AS7C1026B-12TCN	AS7C1026B-12TCN	TSOP I-32	1M	64Kx16	12	0 to 70	4.5 to 5.5	1.91	1.89	1.86
913-AS7C1024B-12JCN	AS7C1024B-12JCN	SOJ-32	1M	125Kx8	12	0 to 70	3.0 to 3.6	1.91	1.89	1.86
913-AS7C31024B-12TCN	AS7C31024B-12TCN	TSOP I-32	1M	125Kx8	12	0 to 70	3.0 to 3.6	1.91	1.89	1.86
913-AS7C31024B12TJCN	AS7C31024B-12TJCN	SOJ-32	1M	125Kx8	12	0 to 70	3.0 to 3.6	1.91	1.89	1.86
913-AS7C31025B12TJCN	AS7C31025B-12TJCN	SOJ-32	1M	125Kx8	12	0 to 70	3.0 to 3.6	1.91	1.89	1.86
913-AS7C31026B-12JCN	AS7C31026B-12JCN	SOJ-32	1M	64Kx16	12	0 to 70	3.0 to 3.6	1.91	1.89	1.86
913-AS7C31026B-12TCN	AS7C31026B-12TCN	TSOP I-32	1M	64Kx16	12	0 to 70	3.0 to 3.6	1.91	1.89	1.86
913-AS7C4096A-12JCN	AS7C4096A-12JCN	SOJ-36	4M	512Kx8	12	0 to 70	4.5 to 5.5	3.73	3.71	3.57
913-AS7C4096A-12TCN	AS7C4096A-12TCN	TSOP II-44	4M	512Kx8	12	0 to 70	4.5 to 5.5	3.73	3.71	3.57
913-AS7C4098A-12JCN	AS7C4098A-12JCN	SOJ-44	4M	256Kx16	12	0 to 70	4.5 to 5.5	3.73	3.71	3.57
913-AS7C4098A-12TCN	AS7C4098A-12TCN	TSOP II-44	4M	256Kx16	12	0 to 70	4.5 to 5.5	3.73	3.71	3.57
913-AS7C34096A-12JCN	AS7C34096A-12JCN	SOJ-36	4M	512Kx8	12	0 to 70	3.0 to 3.6	3.73	3.71	3.57
913-AS7C34096A-12TCN	AS7C34096A-12TCN	TSOP II-44	4M	512Kx8	12	0 to 70	3.0 to 3.6	3.73	3.71	3.57
913-AS7C34098A-12JCN	AS7C34098A-12JCN	SOJ-44	4M	256Kx16	12	0 to 70	3.0 to 3.6	4.73	4.71	4.57
913-AS7C34098A-12TCN	AS7C34098A-12TCN	TSOP II-44	4M	256Kx16	12	0 to 70	3.0 to 3.6	3.73	3.71	3.57

LOW POWER SRAMs

These are devices that typically operate in the 45-ns and slower speed range. These SRAMs are typically designed to consume very low power and are used in applications where power is a major concern. Applications for these SRAMs include digital signal processors (DSPs), PDAs, radios, pagers, consumer electronic products, etc. In these applications, these devices are used for temporary data storage, as well as scratch pad applications. Although Low Power SRAMs have also been around for many years, the recent surge in consumer electronic products have expanded the market for these devices. The density range for these SRAMs is usually from 64K to 8 Mb and are mostly configured with word widths of 8, 16 bits.



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MOUSER STOCK NO.	Alliance Memory Part No.	Package	Density	Organization	Speed (ns)	Temperature Range (°C)	Operating Voltage (V)	Price Each		
								1	25	50
913-AS6C6264A-70PCN	AS6C6264A-70PCN	DIP-28	64K	8Kx8	70	0 to 70	4.5 to 5.5	1.45	1.44	1.43
913-AS6C6264A-70SCN	AS6C6264A-70SCN	SOP-28	64K	8Kx8	70	0 to 70	4.5 to 5.5	1.05	1.03	1.00
913-AS6C62256A-70PCN	AS6C62256A-70PCN	DIP-28	256K	32Kx8	70	0 to 70	4.5 to 5.5	1.30	1.29	1.28
913-AS6C62256A-70SIN	AS6C62256A-70SIN	SOP-28	256K	32Kx8	70	-40 to 85	4.5 to 5.5	1.15	1.14	1.13
913-AS6C1008-55PCN	AS6C1008-55PCN	DIP-32	1M	128Kx8	55	0 to 70	2.7 to 5.5	1.68	1.66	1.63
913-AS6C1008-55SIN	AS6C1008-55SIN	SOP-32	1M	128Kx8	55	-40 to 85	2.7 to 5.5	1.45	1.44	1.43
913-AS6C4008-55PCN	AS6C4008-55PCN	DIP-32	4M	512Kx8	55	0 to 70	2.7 to 5.5	3.27	3.25	3.13
913-AS6C4008-55SIN	AS6C4008-55SIN	SOP-32	4M	512Kx8	55	-40 to 85	2.7 to 5.5	2.97	2.94	2.89
913-AS6C4008-55TIN	AS6C4008-55TIN	TSOP I-32	4M	512Kx8	55	-40 to 85	2.7 to 5.5	2.97	2.94	2.89
913-AS6C4008-55STIN	AS6C4008-55STIN	sTSOP-32	4M	512Kx8	55	-40 to 85	2.7 to 5.5	2.97	2.94	2.89
913-AS6C4008-55ZIN	AS6C4008-55ZIN	TSOP II-32	4M	512Kx8	55	-40 to 85	2.7 to 5.5	3.05	3.01	2.96
913-AS6C4016-55ZIN	AS6C4016-55ZIN	TSOP II-32	4M	256Kx16	55	-40 to 85	2.7 to 5.5	3.05	3.01	2.96
913-AS6C8016-55ZIN	AS6C8016-55ZIN	TSOP II-44	8M	512Kx16	55	-40 to 85	2.7 to 5.5	5.31	5.22	5.13
913-AS6C1616-70BIN	AS6C1616-70BIN	TFBGA-48	16M	1Mx16	70	-40 to 85	2.7 to 3.6	8.98	8.45	8.25

SYNCHRONOUS DRAMs (SDRAM)

These devices are high-speed CMOS synchronous DRAM containing densities from 64M to 256M with a synchronous interface (all signals are registered on the positive edge of the clock signal, CLK). Read and write accesses to the SDRAM are burst oriented; accesses start at a selected location and continue for a programmed number of locations in a programmed sequence. Accesses begin with the registration of a BankActivate command which is then followed by a Read or Write command.

They provide for programmable Read or Write burst lengths of 1, 2, 4, 8, or full page, with a burst termination option. An auto precharge function may be enabled to provide a self-timed row precharge that is initiated at the end of the burst sequence. The refresh functions, either Auto or Self Refresh are easy to use. By having a programmable mode register, the system can choose the most suitable modes to maximize its performance. These devices are well suited for applications requiring high memory bandwidth and particularly well suited to high performance PC applications.



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MOUSER STOCK NO.	Alliance Memory Part No.	Package	Density	Organization	Frequency (MHz)	Temperature Range (°C)	Operating Voltage (V)	Price Each		
								1	25	50
913-AS4C4M16S-7TCN	AS4C4M16S-7TCN	TSOP II-54	64M	4Mx16	143	0 to 70	3.0 to 3.6	4.06	3.26	3.12
913-AS4C8M16S-7TCN	AS4C8M16S-7TCN	TSOP II-54	128M	8Mx16	143	0 to 70	3.0 to 3.6	6.69	6.02	5.62
913-AS4C16M16S-7TCN	AS4C16M16S-7TCN	TSOP II-54	256M	16Mx16	143	0 to 70	3.0 to 3.6	9.27	8.34	7.78

